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Kind regards,

Team Nexperia

# PEMD15; PUMD15

# NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

Rev. 4 — 19 December 2011

**Product data sheet** 

#### 1. Product profile

#### 1.1 General description

NPN/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number			PNP/PNP	NPN/NPN	Package	
	NXP	JEITA	complement	complement	configuration	
PEMD15	SOT666	-	PEMB15	PEMH15	ultra small and flat lead	
PUMD15	SOT363	SC-88	PUMB15	PUMH15	very small	

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or; for the PNP transistor	(TR2) with negat	ive polarity			
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



### 2. Pinning information

Table 3. Pinning

iubic o.	9		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			006aaa143

### 3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMD15	-	plastic surface-mounted package; 6 leads	SOT666	
PUMD15	SC-88	plastic surface-mounted package; 6 leads	SOT363	

### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD15	5E
PUMD15	D0*

[1] \* = placeholder for manufacturing site code

### 5. Limiting values

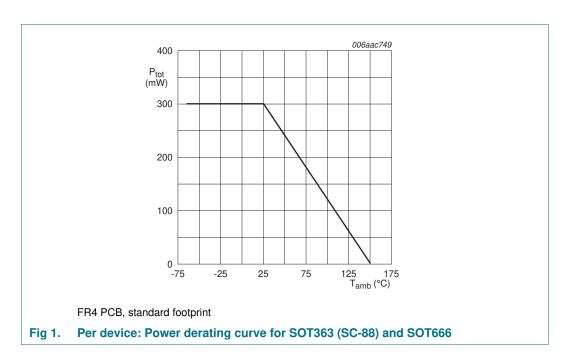
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	(TR2) with negative	e polarity		
$V_{CBO}$	collector-base voltage	open emitter	-	50	٧
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	٧
VI	input voltage TR1				
	positive		-	+30	V
	negative		-	-10	V
	input voltage TR2				
	positive		-	+10	٧
	negative		-	-30	V
lo	output current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMD15 (SOT666)		[1][2] -	200	mW
	PUMD15 (SOT363)		<u>[1]</u> -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMD15 (SOT666)		[1][2] -	300	mW
	PUMD15 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



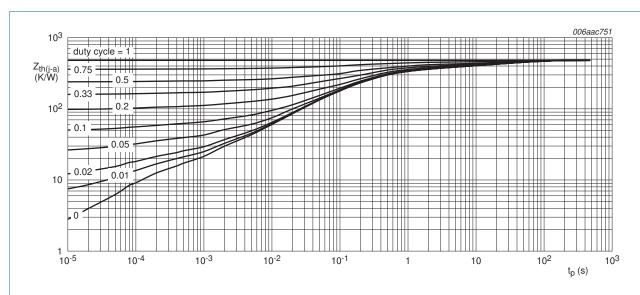
#### 6. Thermal characteristics

Table 7. Thermal characteristics

Parameter	Conditions	ons Min		Max	Unit
Per transistor					
thermal resistance from junction to ambient	in free air				
PEMD15 (SOT666)		<u>[1][2]</u> _	-	625	K/W
PUMD15 (SOT363)		<u>[1]</u> _	-	625	K/W
thermal resistance from junction to ambient	in free air				
PEMD15 (SOT666)		[1][2] -	-	417	K/W
PUMD15 (SOT363)		[1] -	-	417	K/W
	thermal resistance from junction to ambient PEMD15 (SOT666) PUMD15 (SOT363)  thermal resistance from junction to ambient PEMD15 (SOT666)	thermal resistance from junction to ambient  PEMD15 (SOT666)  PUMD15 (SOT363)  thermal resistance from junction to ambient  PEMD15 (SOT666)	thermal resistance from junction to ambient  PEMD15 (SOT666)  PUMD15 (SOT363)  thermal resistance from junction to ambient  PEMD15 (SOT666)  [1][2] -	thermal resistance from junction to ambient  PEMD15 (SOT666)  PUMD15 (SOT363)  thermal resistance from junction to ambient  PEMD15 (SOT666)  [1][2]	thermal resistance from junction to ambient  PEMD15 (SOT666)  PUMD15 (SOT363)  III 625  thermal resistance from junction to ambient  PEMD15 (SOT666)  IIII 417

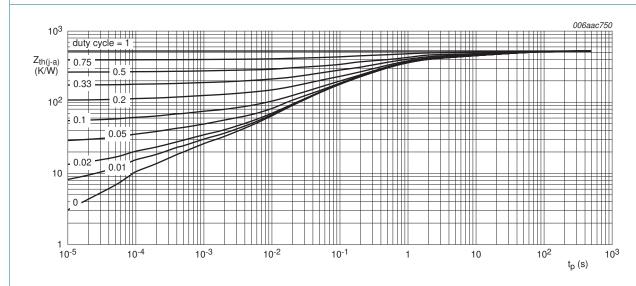
<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMD15 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMD15 (SOT363); typical values

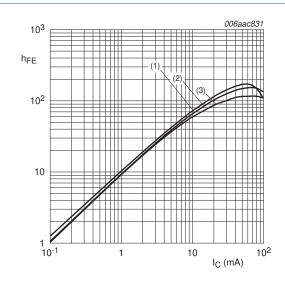
#### 7. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor; for the PNP trans	sistor (TR2) with negative	oolarity			
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub> collector-emitter cut-off current	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	5	μА	
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	900	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2.5	1.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	рF
	TR2 (PNP)		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	[ <u>1]</u>			
	TR1 (NPN)		-	230	-	MHz
	TR2 (PNP)		-	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor



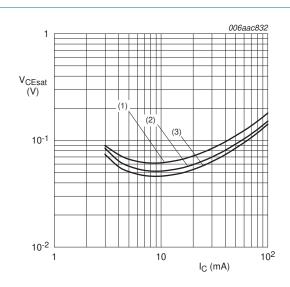
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. TR1 (NPN): DC current gain as a function of collector current; typical values



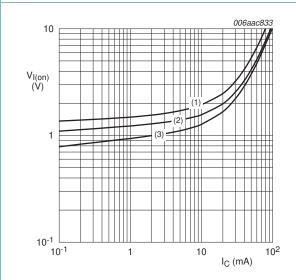
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



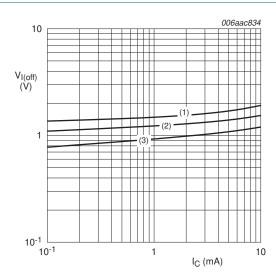
$$V_{CE} = 0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. TR1 (NPN): On-state input voltage as a function of collector current; typical values



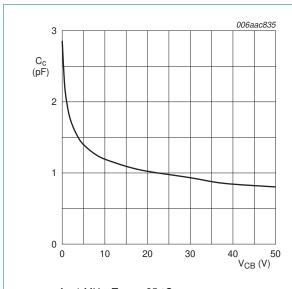
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

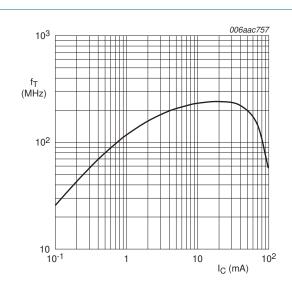
(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. TR1 (NPN): Off-state input voltage as a function of collector current; typical values



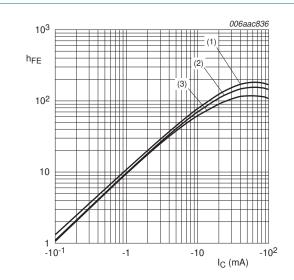
 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig 9. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



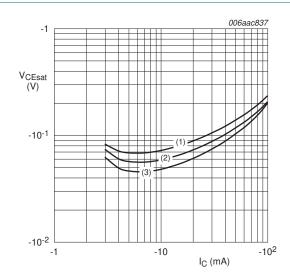
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 10. TR2 (PNP): DC current gain as a function of collector current; typical values



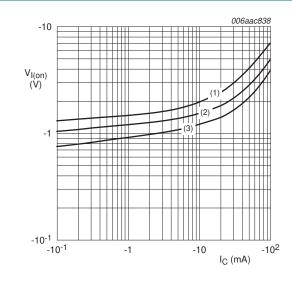
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

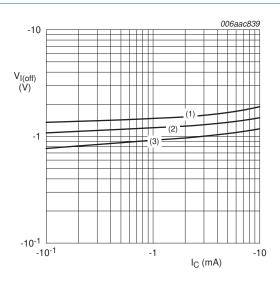
Fig 11. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE} = -0.3 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 12. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 13. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

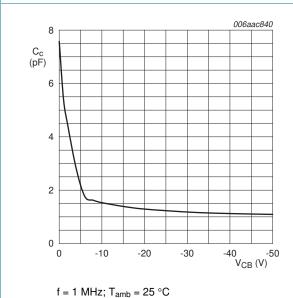
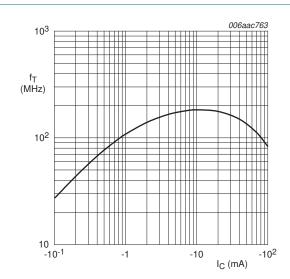


Fig 14. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

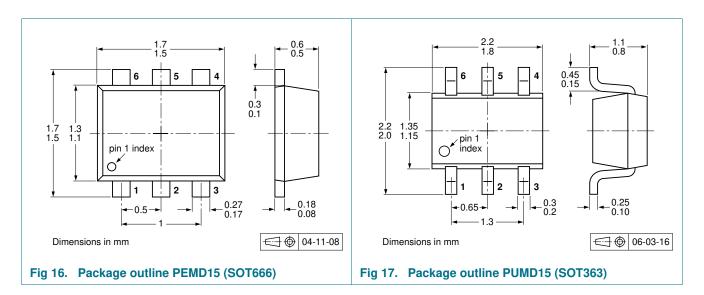
Fig 15. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

#### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 9. Package outline



### 10. Packing information

Table 9. Packing methods

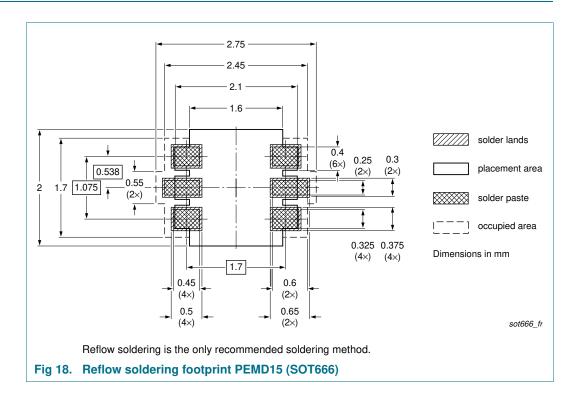
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

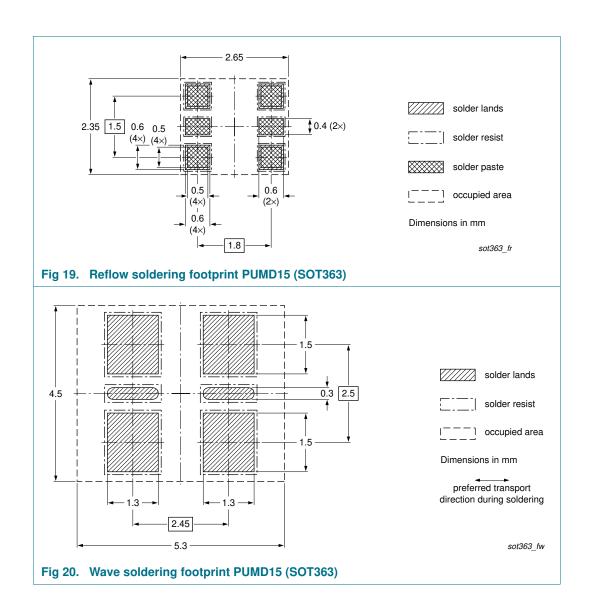
Туре	Package Description			Packing quantity			
number				3000	4000	8000	10000
PEMD15	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
	4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMD15	SOT363	4 mm pitch, 8 mm tape and reel; T1	2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	3]	-125	-	-	-165

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

PEMD15\_PUMD15

### 11. Soldering





### 12. Revision history

Table 10. Revision history

	-			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMD15_PUMD15 v.4	20111219	Product data sheet	-	PEMD15_PUMD15 v.3
Modifications:	Section 1 "F	Product profile": updated		
	<ul> <li>Section 4 "N</li> </ul>	Marking": updated		
	• Figure 1 to	3, 8, 9, 14 and 15: added		
	Section 6 "	Thermal characteristics": up	dated	
	• Figure 4 to	7, <u>10</u> to <u>13</u> : updated		
	• <u>Table 8 "Ch</u>	aracteristics": I <sub>CEO</sub> updated	, f <sub>T</sub> added	
	<ul> <li>Section 8 ""</li> </ul>	Test information": added		
	Section 11 '	<u>'Soldering"</u> : added		
	Section 13	<u>"Legal information"</u> : update	d	
PEMD15_PUMD15 v.3	20090902	Product data sheet	-	PEMD15_PUMD15 v.2
PEMD15_PUMD15 v.2	20050425	Product data sheet	-	PUMD15 v.1
PUMD15 v.1	20040204	Product specification	-	-
-				

#### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMD15\_PUMD15

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PEMD15; PUMD15

NPN/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ 

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## PEMD15; PUMD15

NPN/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 4.7 kΩ

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.